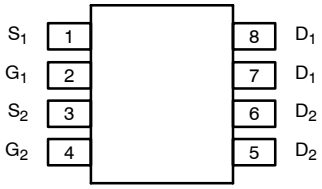
Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-30	0.080 @ V_{GS} = -10 V	-3.9
	0.135 @ V_{GS} = -4.5 V	-3.0

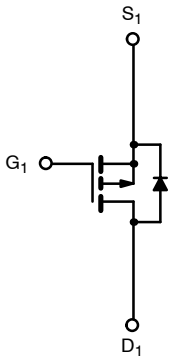
TrenchFET® Power MOSFETs

SO-8

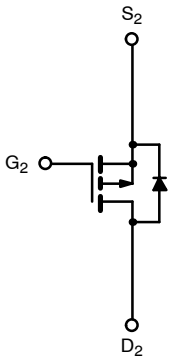


Top View

Ordering Information: Si4947ADY
Si4947ADY-T1 (with Tape and Reel)



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	±20		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	-3.9	-3.0	A
	T_A = 70°C		-3.1	-2.4	
Pulsed Drain Current		I_{DM}	-20		
continuous Source Current (Diode Conduction)[a]		I_S	-1.7	-1.0	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.0	1.2	W
	T_A = 70°C		1.3	0.76	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	54	62.5	°C/W
	Steady State		87	105	
Maximum Junction-to-Foot	Steady State	R_{thJF}	34	45	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

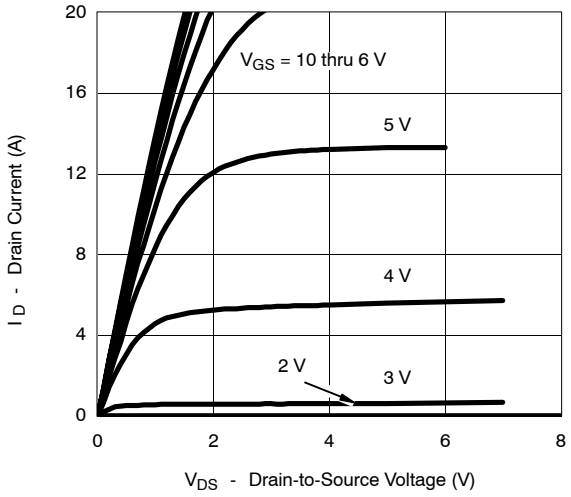
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 μA	-1.0			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30 V, V_{GS} = 0 V			-1	μA
		V_{DS} = -30 V, V_{GS} = 0 V, T_J = 70°C			-10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -10 V	-15			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = -10 V, I_D = -3.9 A		0.062	0.080	Ω
		V_{GS} = -4.5 V, I_D = -3.0 A		0.105	0.135	
Forward Transconductance[a]	g_{fs}	V_{DS} = -15 V, I_D = -2.5 A		5.0		S
Diode Forward Voltage[a]	V_{SD}	I_S = -1.7 A, V_{GS} = 0 V		-0.82	-1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -5 V, I_D = -3.9 A		5.8	8	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			1.9		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 10 Ω I_D ≅ -1 A, V_{GEN} = -10 V, R_G = 6 Ω		8	15	ns
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			21	40	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = -1.7 A, di/dt = 100 A/μs		27	40	

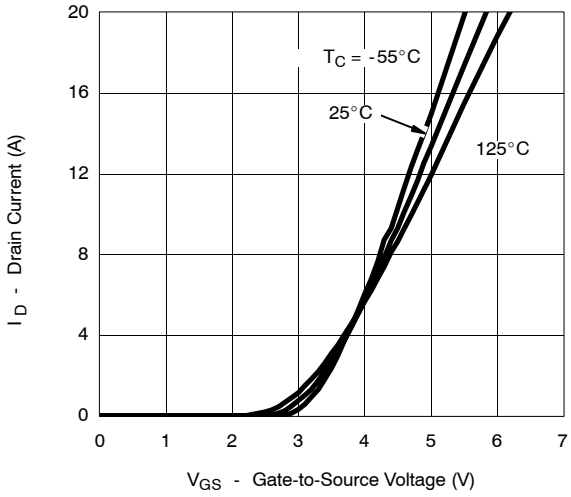
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

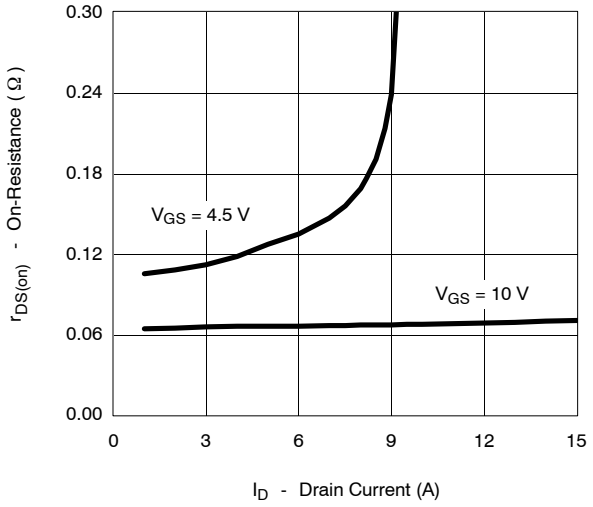


Transfer Characteristics

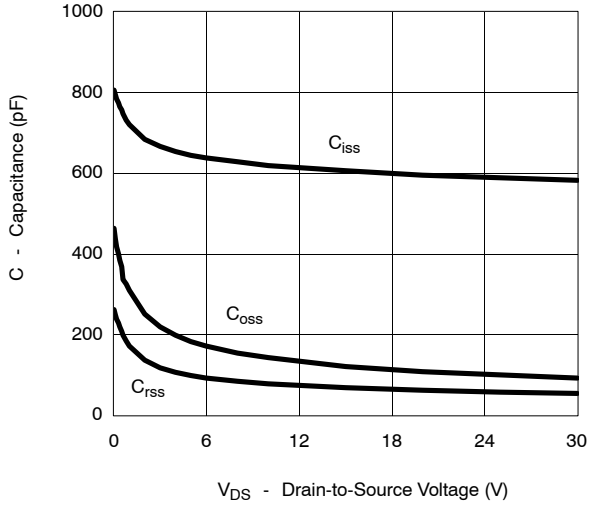


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

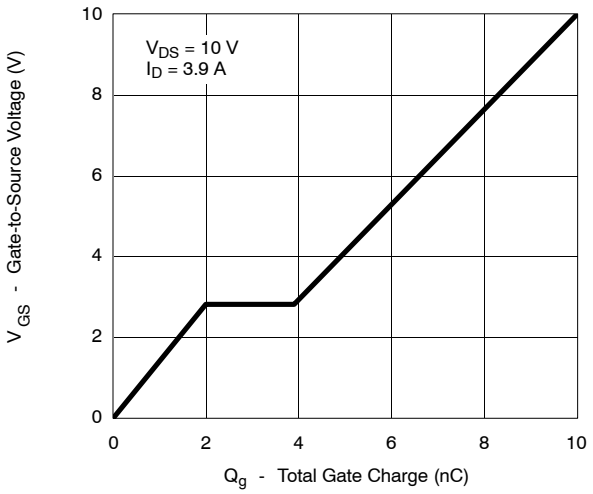
On-Resistance vs. Drain Current



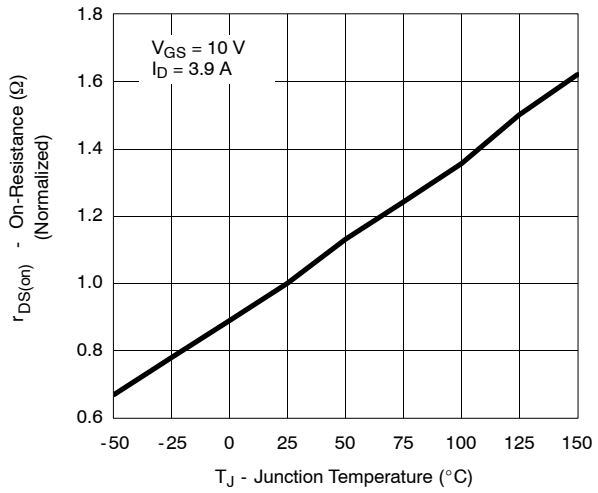
Capacitance



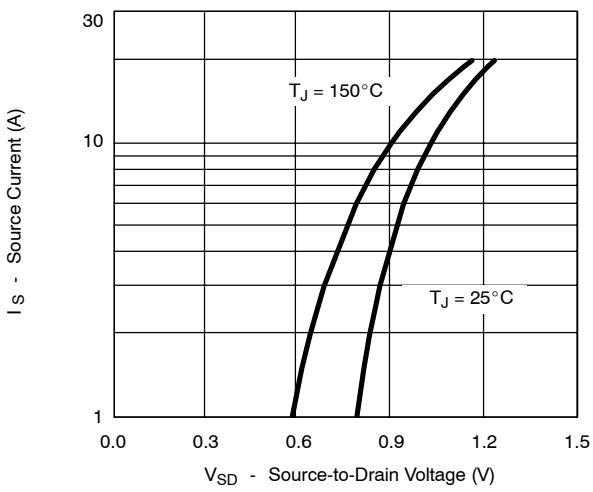
Gate Charge



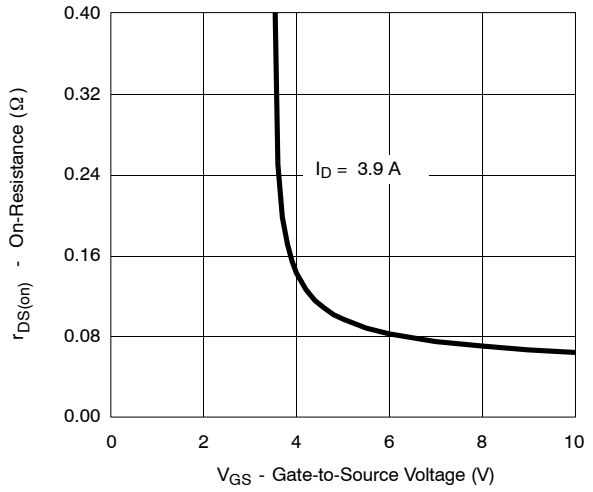
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

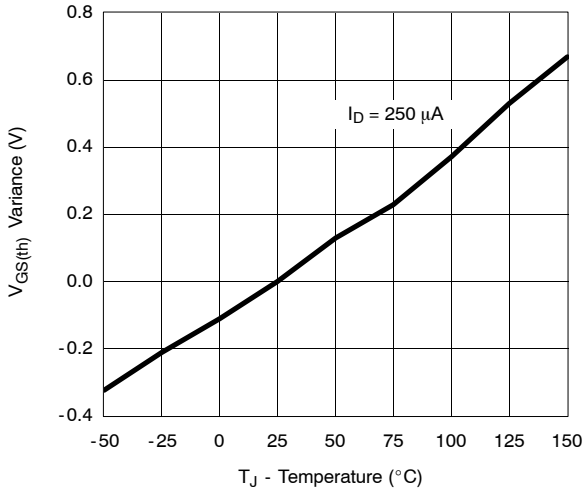


On-Resistance vs. Gate-to-Source Voltage

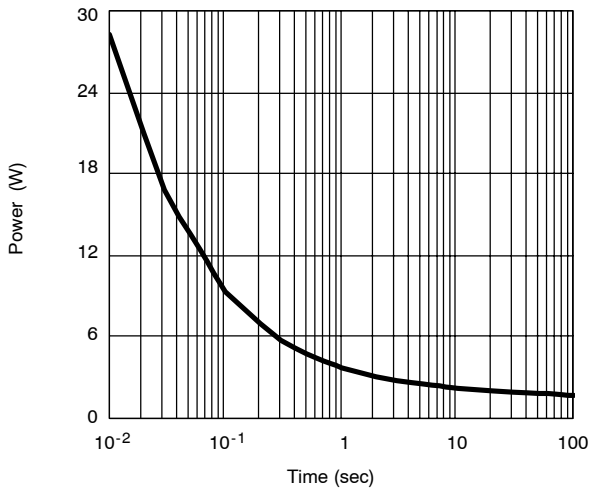


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

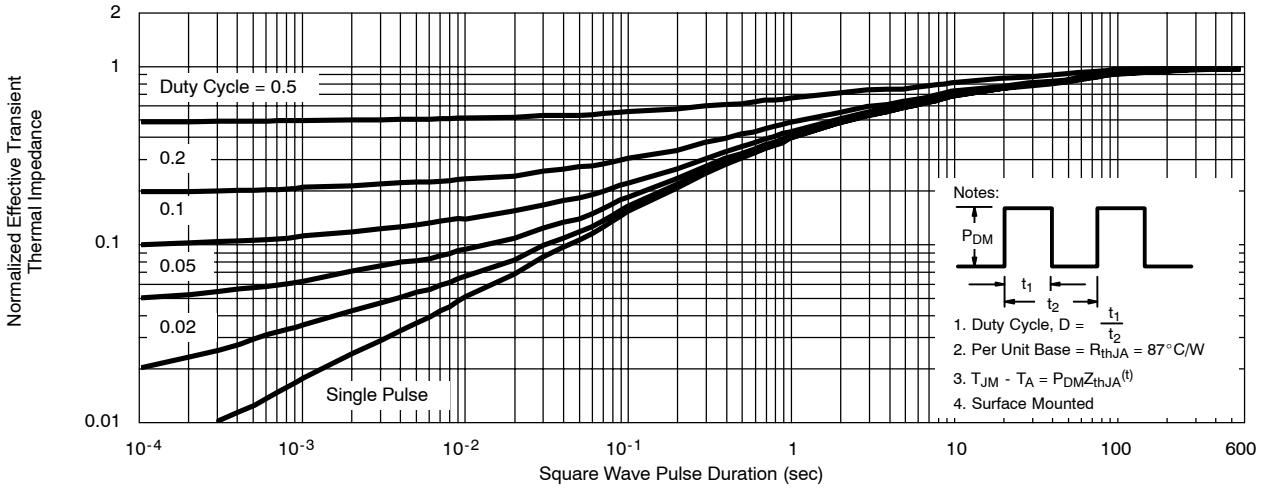
Threshold Voltage



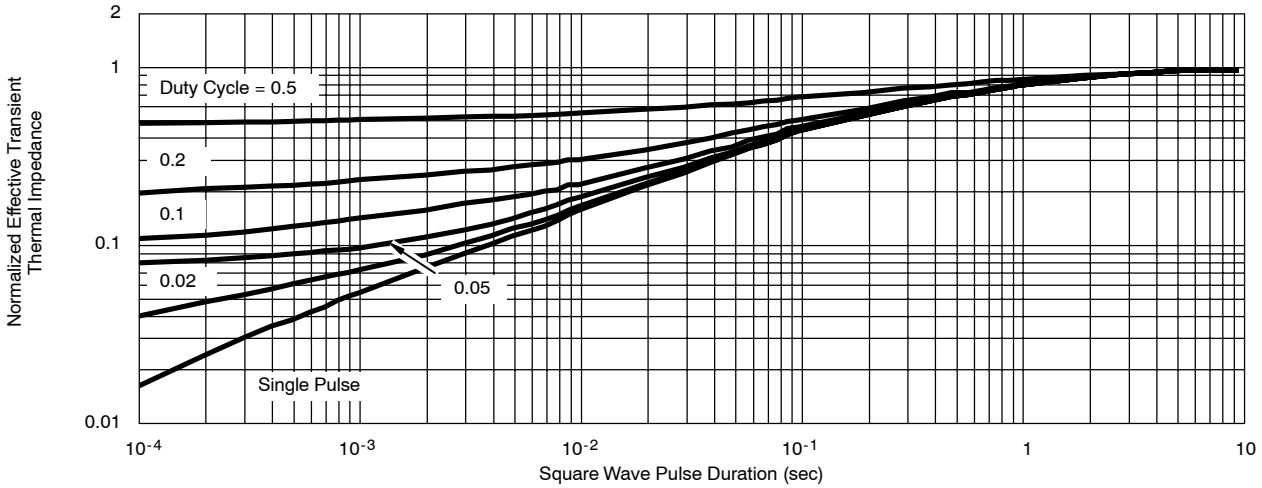
Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



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